Fig.1

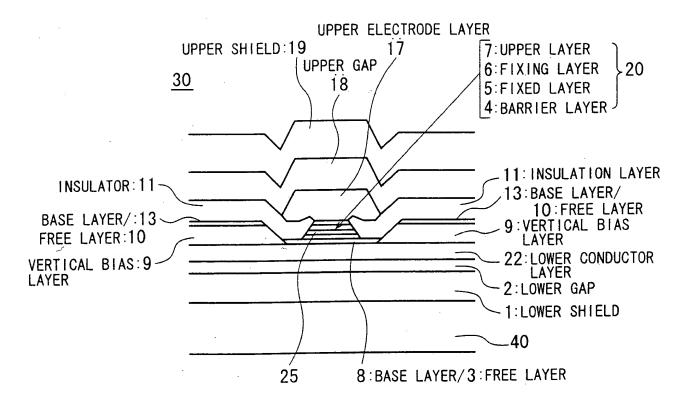


Fig.2

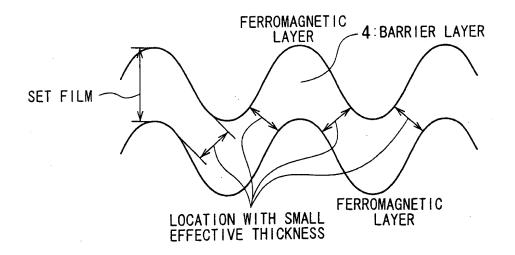


Fig.3

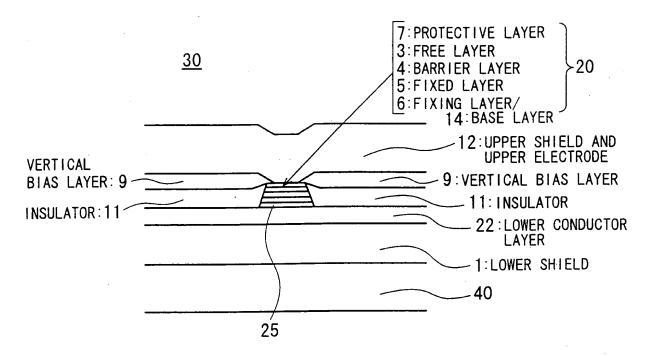
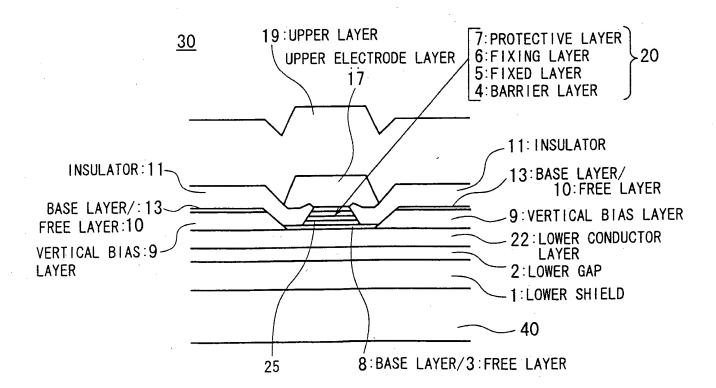


Fig.4





Invention Title: Magnetoresistive Effect Sensor
Inventor: Hayashi, Kazuhiko
Det No./Application No: NEC2370-US:09/853,022
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Fig.5

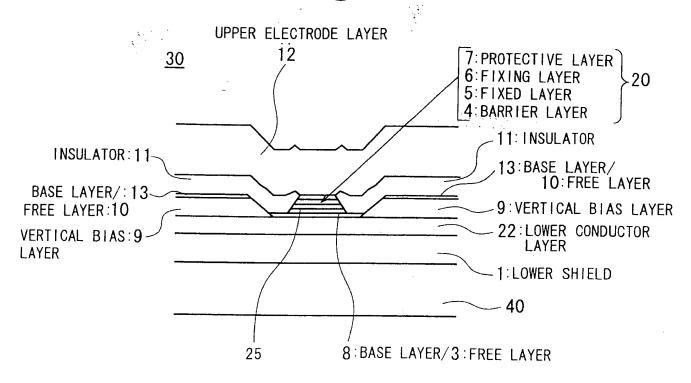


Fig.6

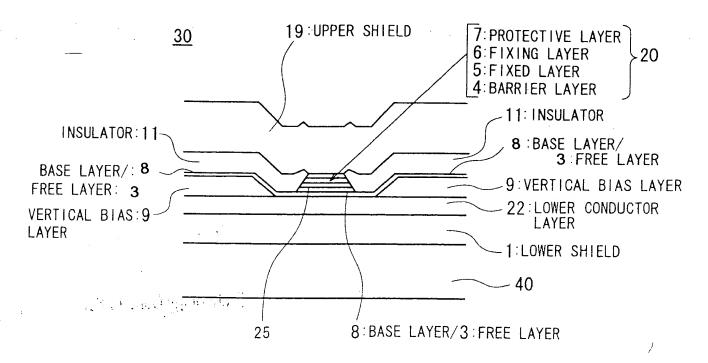


Fig.7

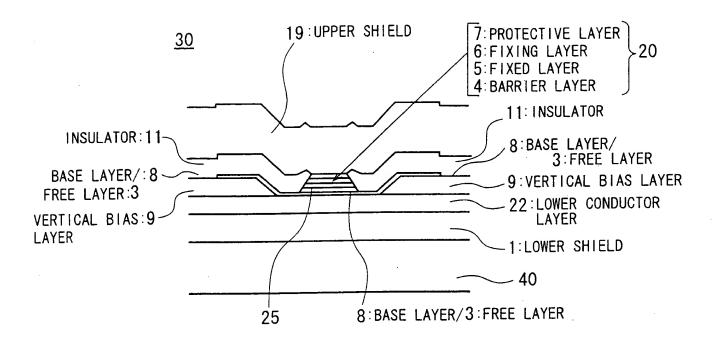


Fig.8

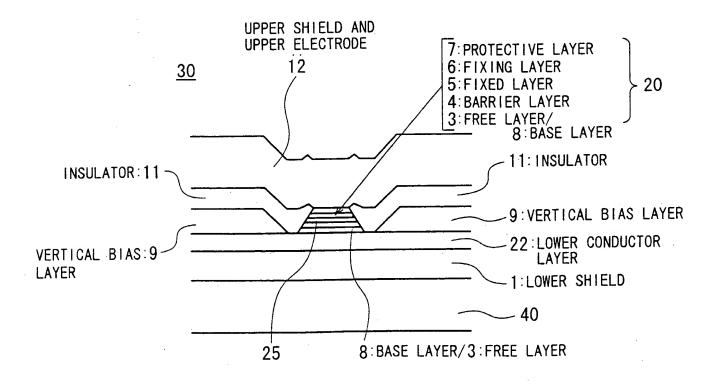
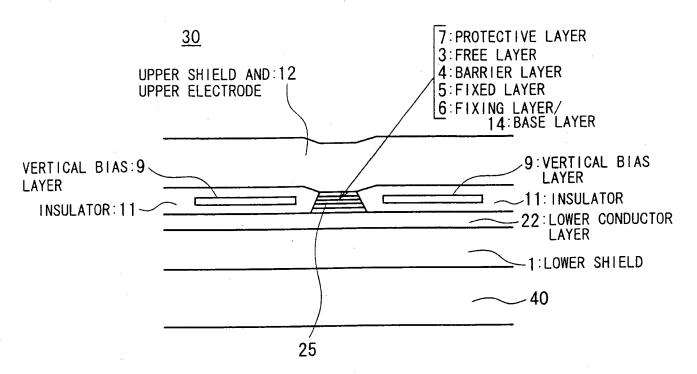
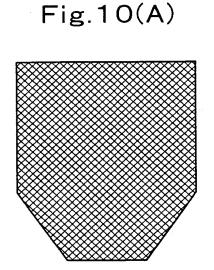


Fig.9





LOWER SHIELD AND LOWER CONDUCTOR LAYER FORMED AS FILMS AND PATTERNED (PR FORMATION \rightarrow PR REMOVAL)

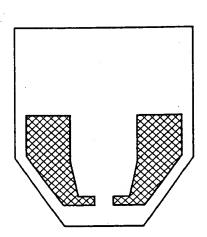


Fig. 10(B)

VERTICAL BIAS LAYER BASE LAYER/VERTICAL BIAS LAYER FILM FORMATION AND PATTERNING (PR FORMATION \rightarrow PR REMOVAL)

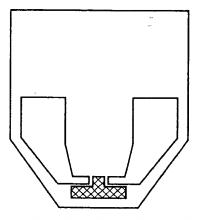


Invention Title: Magnetoresistive Effect Sensor Inventor: Hayashi, Kazuhiko Do, et No./Application No: NEC2370-US:09/853,6

Replacement Sheet

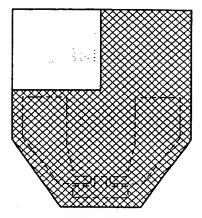
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Fig. 11(A)



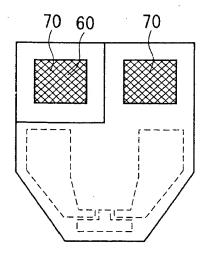
MAGNETORESISTIVE EFFECT FILM \rightarrow PR FORMATION \rightarrow MILLING \rightarrow INSULATION FILM FORMATION \rightarrow LIFT-OFF

Fig.11(B)



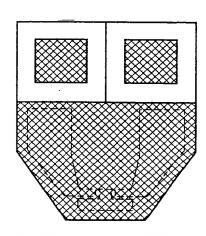
UPPER SHIELD FORMATION → PR FORMATION → PATTERNING → PR REMOVAL

Fig. 12(A)



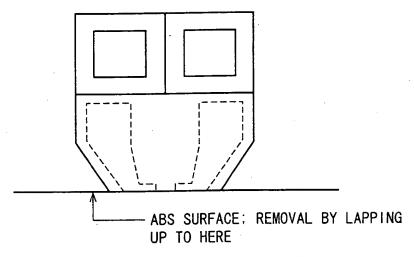
LOWER ELECTRODE HOLE FORMATION. ELECTRODE TERMINAL FORMATION

Fig. 12(B)



RECORDING HEAD FORMATION

Fig.13



FORMATION OF ABS SURFACE BY LAPPING

Fig.14

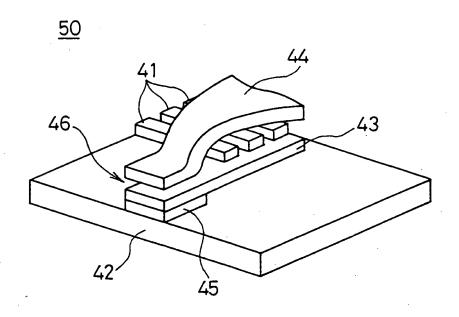


Fig.15

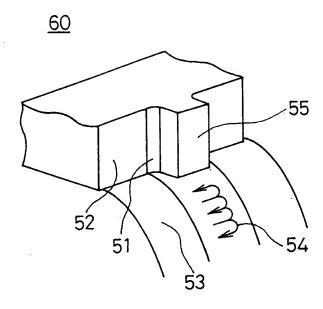


Fig.16

